^{32}Si β^- decay (157 y)

Type	Author	History Citation	Literature Cutoff Date
Full Evaluation	Jun Chen	NDS 201,1 (2025)	31-Oct-2024

Parent: ^{32}Si: E=0; $J^\pi=0^+$; $T_{1/2}$=157 y *7*; Q(β^-)=227.2 *3*; %β^- decay=100
^{32}Si-$T_{1/2}$: From Adopted Levels of ^{32}Si.
^{32}Si-Q(β^-): From 2021Wa16.
See comments for $T_{1/2}$ of ^{32}Si g.s. in Adopted Levels of ^{32}Si for all references on $T_{1/2}$ of ^{32}Si β^- decay.
Other: 1984Po09 (end-point energy).

^{32}P Levels

E(level)	J^π
0	1^+

β^- radiations

E(decay)	E(level)	Iβ^-[†]	Log *ft*	Comments
(227.2 *15*)	0	100	8.22 *2*	av Eβ=69.59 *10* Iβ^-: it is assumed ^{32}Si decays only to ^{32}P g.s., considering Q(β^-)=227.2 *3* and the decay to the only energetically-allowed excited level at E=78 with $J^\pi=2^+$ is unlikely.

[†] Absolute intensity per 100 decays.